In the claims:

Claims 1-14 (Canceled).

15. (Original) A method of forming a multichip module comprising the steps of:

forming a thin film structure on a temporary carrier;

attaching an electrically insulating frame to a first surface of the thin film structure;

attaching at least one semiconductor device to the first surface of the thin film structure;

removing the temporary carrier; and

attaching at least one semiconductor device to a second surface of the thin film structure, wherein the first surface is opposed to the second surface and wherein there is interconnectivity through the thin film structure between the semiconductor devices and the frame.

16. (Original) The method of claim 15 wherein the frame comprises an open area through which at least one semiconductor device is exposed.

17. (Original) The method of claim 15 further comprising the step of applying a stiffening material between the frame and one of the at least one semiconductor devices.

18. (New) The method of claim 17 wherein the stiffening material is epoxy.

19. (New) The method of claim 1 wherein the thin film structure has a thickness of 15 to 250 microns.

20. (New) The method of claim 1 wherein the electrically insulating frame comprises a ceramic or organic material.

21. (New) The method of 1 further comprising the step of attaching at least one passive

component on one of the opposed surfaces of the thin film structure.